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METHOD OF FORMING CONDUCTIVE PLUG

ABSTRACT OF THE DISCLOSURE

10 A method of forming a conductive plug is disclosed. A device with a conductive region is formed on a semiconductor substrate. An insulating layer is formed on the semiconductor substrate. The insulating layer is etched to form a contact window which exposes the conductive region of the device. A diffusion barrier layer is formed on the exposed conductive region and the periphery of the contact window. A hydrogen plasma
15 treatment is performed in a reaction chamber; and a conductive material is filled in the contact window, to form the conductive plug.

FIGURE 2

